

# N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
30	0.060 at V <sub>GS</sub> = 10 V	3.6	2.1 nC			
30	0.075 at V <sub>GS</sub> = 4.5 V	3.6	2.1110			

#### **FEATURES**

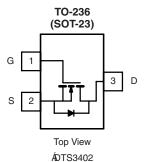
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC

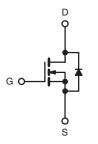


ROHS COMPLIANT HALOGEN FREE

#### **APPLICATIONS**

DC/DC Converter





N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	IGS T <sub>A</sub> = 25 °C,	unless othe	erwise noted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	± 20	]	
	T <sub>C</sub> = 25 °C		3.6 <sup>a</sup>		
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	3.3		
Continuous Brain Carrotti (1) = 100 °C)	T <sub>A</sub> = 25 °C	'D 1	3.3		
	T <sub>A</sub> = 70 °C		2.7	Α	
Pulsed Drain Current		I <sub>DM</sub>	15		
	T <sub>C</sub> = 25 °C		1.4		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	IS	0.9 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		1.7	w	
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	1.1		
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	, n	1.1 <sup>b, c</sup>	] **	
	T <sub>A</sub> = 70 °C		0.7 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>			260		

THERMAL RESISTANCE RATI	NGS				
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 5 s	$R_{thJA}$	90	115	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	60	75	0/11

#### Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 130 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static						•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA		31		m\//°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA		- 5		mV/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1.2		2.2	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zawa Cata Waltana Dunin Courset		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
		$V_{GS} = 10 \text{ V}, I_D = 3.2 \text{ A}$	4.4		0.060	_	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$		0.061	0.075	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.8 A		11		S	
Dynamic <sup>b</sup>				_	I 	<u> </u>	
Input Capacitance	C <sub>iss</sub>			235			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		45		pF nC	
Reverse Transfer Capacitance	C <sub>rss</sub>			17			
		$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$		4.5	6.7		
Total Gate Charge	$Q_g$			2.1	3.2		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 3.4 \text{ A}$		0.85		nC	
Gate-Drain Charge	$Q_{gd}$			0.65			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.8	4.4	8.8	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			12	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 5.6 $\Omega$		50	75		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 2.7 A, $V_{GEN}$ = 4.5 V, $R_g$ = 1 $\Omega$		12	20	1	
Fall Time	t <sub>f</sub>			22	35		
Turn-On Delay Time	t <sub>d(on)</sub>			5	10	ns	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 5.6 $\Omega$		12	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 2.7 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		10	15		
Fall Time	t <sub>f</sub>			5	10		
<b>Drain-Source Body Diode Characteristic</b>	cs			1			
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			1.4	۸	
Pulse Diode Forward Current	I <sub>SM</sub>				15	A	
Body Diode Voltage	$V_{SD}$	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			10	20	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	1 0.7 A dl/dt 100 A/v- T 05 00		5	10	nC	
Reverse Recovery Fall Time	ta	$I_F = 2.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		6			
Reverse Recovery Rise Time	t <sub>b</sub>			4		ns	

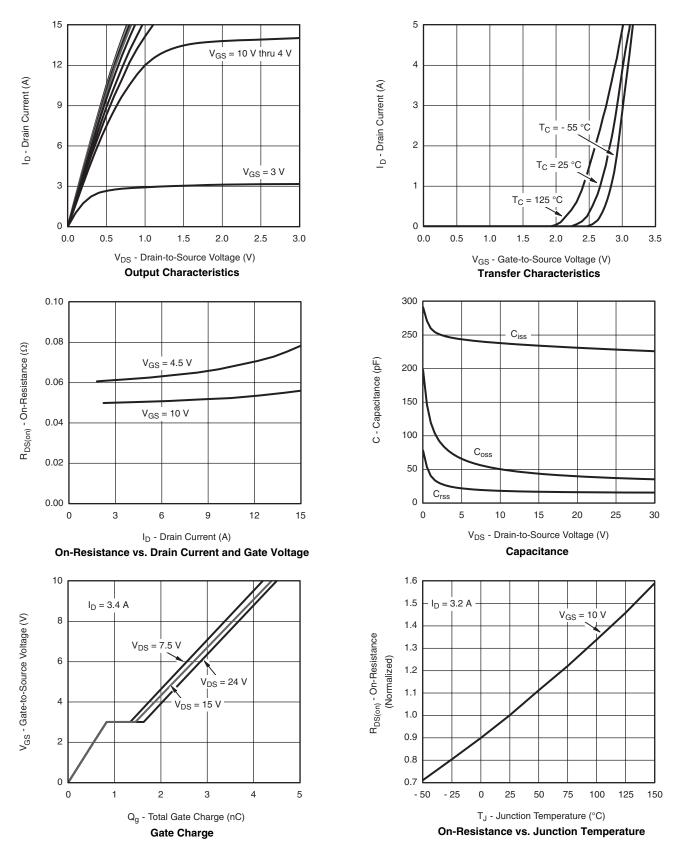
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

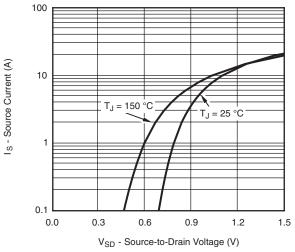


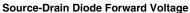
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

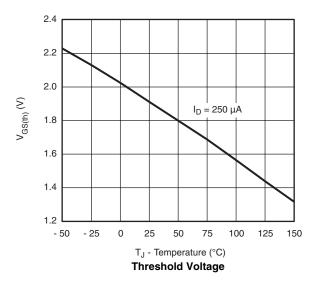


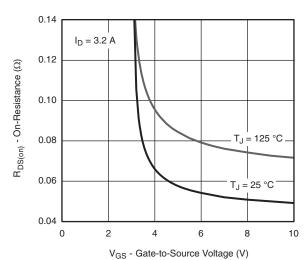


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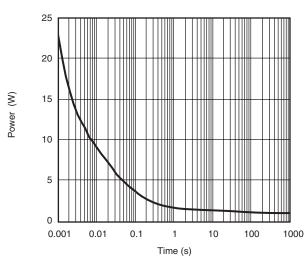




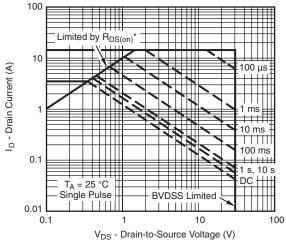




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power

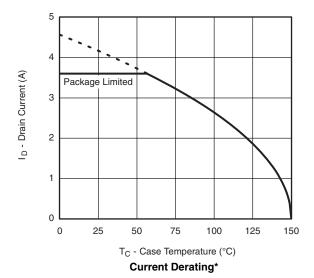


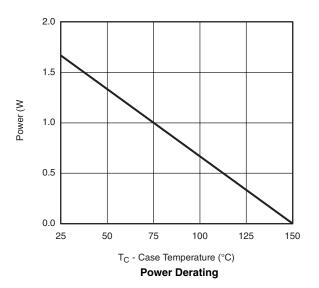
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

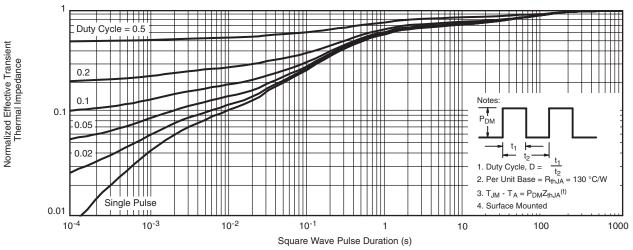




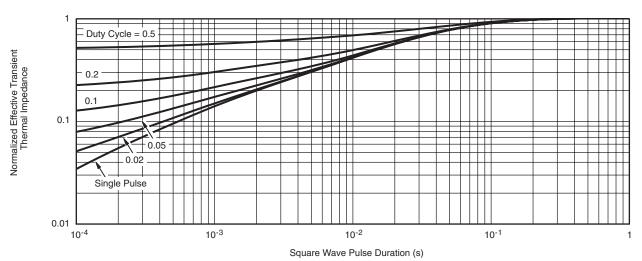
 $<sup>^*</sup>$  The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



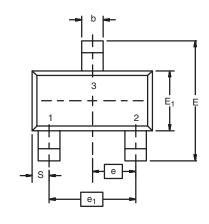
Normalized Thermal Transient Impedance, Junction-to-Ambient

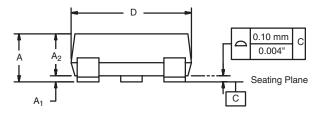


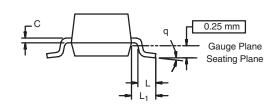
Normalized Thermal Transient Impedance, Junction-to-Foot



# SOT-23 (TO-236): 3-LEAD





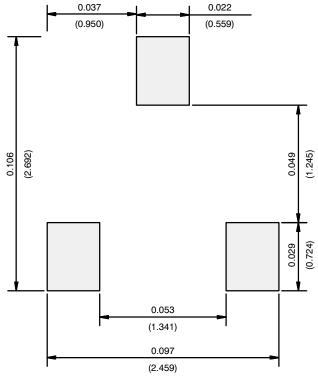


Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
Α	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
С	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
е	0.95	0.95 BSC		4 Ref
e <sub>1</sub>	1.90	1.90 BSC		8 Ref
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025	5 Ref
S	0.50 Ref		0.020	) Ref
q	3°	8°	3°	8°

DWG: 5479



#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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